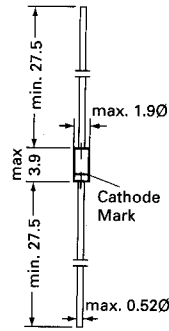


# 1N 914 ...1N 4454

## SILICON EPITAXIAL PLANAR DIODE

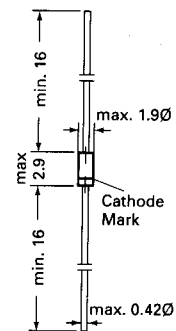
**Silicon Epitaxial Planar Diode**  
for general purpose and switching.

The types 1N4149, 1N4447 and 1N4449 are also available in glass case DO-34.



Glass case JEDEC DO-35

Dimensions in mm



Glass case JEDEC DO-34

Dimensions in mm

branded on reel  
or AMMOPAK

Type	Peak reverse voltage $V_{RM}$ V	Max. aver. rectified current $I_o$ mA	Max. power dissip. at 25 °C $P_{tot}$ mW	Max. junction temperature $T_j$ °C	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
					$V_F$ V	at $I_F$ mA	$I_R$ nA	at $V_R$ V	$t_{rr}$ ns	Conditions
1N914	100	75	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4149 <sup>1)</sup>	100	150	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4150	50	200	500	200	1.0	200	100	50	max. 4.0	$I_F = I_R = 10$ to 200 mA, to $0.1 I_F$
1N4151	75	150	500	200	1.0	50	50	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4152	40	150	400	175	0.55	0.10	50	30	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4153	75	150	400	175	0.55	0.10	50	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4154	35	150 <sup>2)</sup>	500	200	1.0	30	100	25	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4447 <sup>1)</sup>	100	150	500	200	1.0	20	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4449 <sup>1)</sup>	100	150	500	200	1.0	30	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$ , to $I_R = 1$ mA
1N4450	40	150	400	175	0.54	0.50	50	30	max. 4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
1N4451	40	150	400	175	0.50	0.10	50	30	max. 10	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1.0	10	100	50	max. 4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA

<sup>1)</sup> These diodes are also available in glass case DO-34.

<sup>2)</sup> Valid provided that leads at a distance of 8mm from case are kept at ambient temperature.

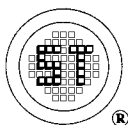
Parameters for diodes in case DO-34:

$$P_{tot} = 300 \text{ mW}$$

$$T_j = 175 \text{ °C}$$

$$T_s = -65 \text{ to } +175 \text{ °C}$$

$$R_{thA} = \leq 0.4 \text{ K/mW}$$



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